PMEG2010BELD

20 V, 1 A low VF MEGA Schottky barrier rectifier Rev. 1 — 18 April 2012

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small DFN1006D-2 (SOD882D) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

1.2 Features and benefits

- Average forward current: I_{F(AV)} ≤ 1 A
- Reverse voltage: V_R ≤ 20 V
- Low forward voltage V_F ≤ 490 mV
- AEC-Q101 qualified

- Ultra small and leadless SMD plastic package
- Solderable side pads
- Package height typ. 0.37 mm

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications
- Ultra high-speed switching
- LED backlight for mobile application

1.4 Quick reference data

Quick reference data Table 1.

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|-------------------------|---|------------|-----|-----|-----|------|
| I _{F(AV)} | average forward current | δ = 0.5 ; f = 20 kHz; $T_{amb} \le$ 80 °C; square wave | <u>[1]</u> | - | - | 1 | Α |
| | | δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 130 °C; square wave | | - | - | 1 | Α |
| V_R | reverse voltage | T _j = 25 °C | | - | - | 20 | V |
| V _F | forward voltage | I_F = 1 A; pulsed; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C | | - | 428 | 490 | mV |
| I_R | reverse current | V _R = 10 V; T _j = 25 °C | | - | 28 | 50 | μΑ |
| t _{rr} | reverse recovery time | $I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$ | | - | 1.6 | - | ns |

^[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|-------------------------|--------------------|
| 1 | K | cathode[1] | | . [4] |
| 2 | Α | anode | 1 2 | 1 [K] 2 |
| | | | | sym001 |
| | | | Transparent top view | |
| | | | DFN1006D-2 | |
| | | | (SOD882D) | |

^[1] The marking bar indicates the cathode.

3. Ordering information

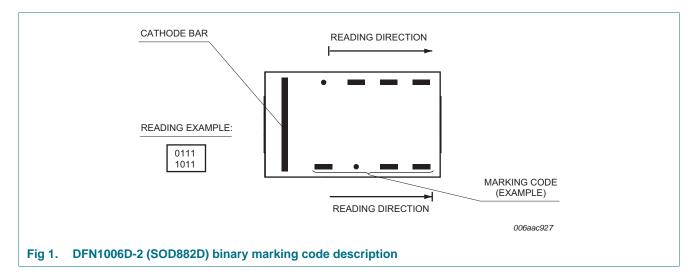
Table 3. Ordering information

| Type number | Package | | | | | | |
|--------------|------------|---|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| PMEG2010BELD | DFN1006D-2 | Leadless ultra small plastic package; 2 terminals | SOD882D | | | | |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| PMEG2010BELD | 0000 1001 |



5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| | | · · · · · · · · · · · · · · · · · · · | | | | |
|--------------------|-------------------------------------|--|------------|-----|------|------|
| Symbol | Parameter | Conditions | | Min | Max | Unit |
| V_R | reverse voltage | T _j = 25 °C | | - | 20 | V |
| I _F | forward current | T _{sp} ≤ 130 °C | | - | 1 | Α |
| I _{F(AV)} | average forward current | δ = 0.5 ; f = 20 kHz; square wave; T _{amb} ≤ 80 °C | <u>[1]</u> | - | 1 | Α |
| | | δ = 0.5 ; f = 20 kHz; square wave; T _{sp} ≤ 130 °C | | - | 1 | Α |
| I _{FRM} | repetitive peak forward current | $t_p \le 1 \text{ ms}; \delta \le 0.25$ | | - | 3 | Α |
| I _{FSM} | non-repetitive peak forward current | $t_p = 8 \text{ ms}; T_{j(init)} = 25 \text{ °C}; \text{ square wave}$ | | - | 6 | Α |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [2][3] | - | 370 | mW |
| | | | [4][3] | - | 735 | mW |
| | | | [1][3] | - | 1135 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| | | | | | | |

^[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|------------|------------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance | [1][4][3 | [1][2][3] | - | - | 340 | K/W |
| | from junction to ambient | | [1][4][3] | - | - | 170 | K/W |
| | | | [1][5][3] | - | - | 110 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | <u>[6]</u> | - | - | 25 | K/W |

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Reflow soldering is the only recommended soldering method.

^[4] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode 1 cm².

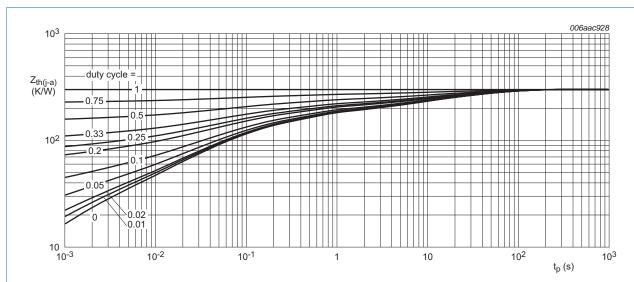
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Reflow soldering is the only recommended soldering method.

^[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

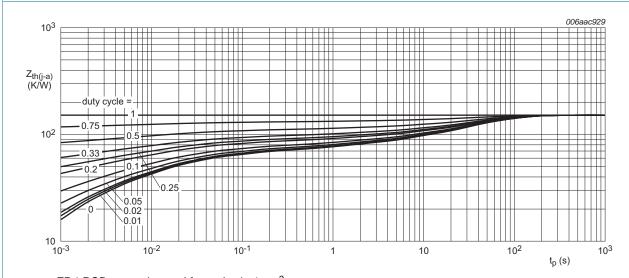
^[5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

^[6] Soldering point of cathode tab.



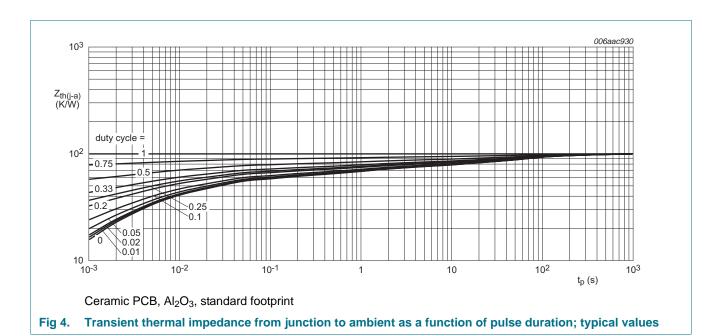
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm²

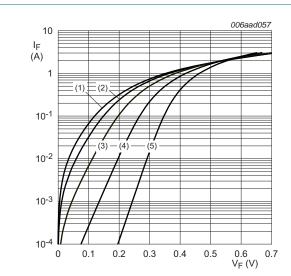
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



7. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|--------------------------|---|-----|-----|-----|------|
| V _F | forward voltage | I_F = 100 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02 ; T_j = 25 °C | - | 266 | 310 | mV |
| | | I_F = 500 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_j = 25 °C | - | 353 | 390 | mV |
| | | I_F = 1 A; pulsed; $t_p \le 300~\mu s; \delta \le 0.02$; T_j = 25 °C | - | 428 | 490 | mV |
| I _R | reverse current | $V_R = 10 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 28 | 50 | μΑ |
| | | V _R = 20 V; T _j = 25 °C | - | 87 | 200 | μΑ |
| C _d | diode capacitance | $V_R = 1 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$ | - | 31 | 40 | pF |
| t _{rr} | reverse recovery time | $I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$ | - | 1.6 | - | ns |
| V_{FRM} | forward recovery voltage | $I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C}$ | - | 565 | - | mV |
| | | | | | | |



(1)
$$T_i = 150 \, ^{\circ}\text{C}$$

(2)
$$T_i = 125 \, ^{\circ}C$$

(3)
$$T_i = 85 \, ^{\circ}C$$

(4)
$$T_j = 25 \, ^{\circ}C$$

(5)
$$T_j = -40 \, ^{\circ}\text{C}$$

Fig 5. Forward current as a function of forward voltage; typical values

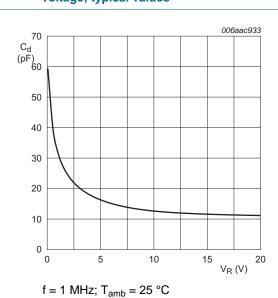
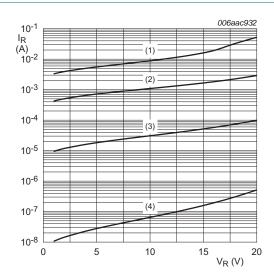


Fig 7. Diode capacitance as a function of reverse voltage; typical values



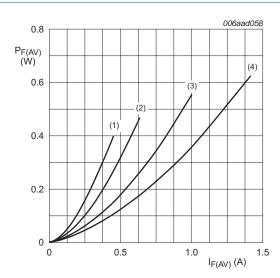
(1)
$$T_j = 125 \, ^{\circ}C$$

(2)
$$T_i = 85 \, ^{\circ}C$$

(3)
$$T_j = 25 \, {}^{\circ}\text{C}$$

(4)
$$T_i = -40 \, ^{\circ}\text{C}$$

Fig 6. Reverse current as a function of reverse voltage; typical values



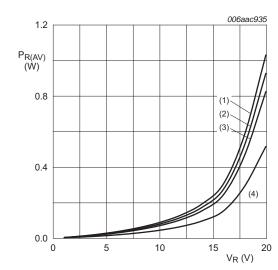
(1)
$$\delta = 0.1$$

(2)
$$\delta = 0.2$$

(3)
$$\delta = 0.5$$

(4)
$$\delta = 1$$

Fig 8. Average forward power dissipation as a function of average forward current; typical values



T_i = 125 °C

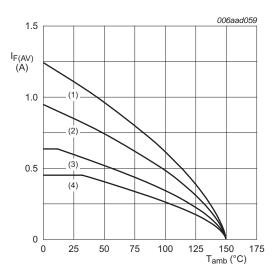
(1) $\delta = 1$ (DC)

(2) $\delta = 0.9$; f = 20 kHz

(3) $\delta = 0.8$; f = 20 kHz

(4) $\delta = 0.5$; f = 20 kHz

Fig 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_j = 150 °C

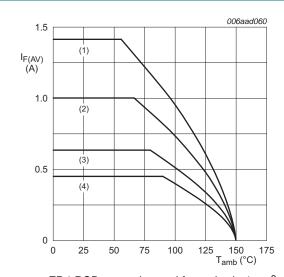
(1) $\delta = 1$

(2) $\delta = 0.5$

(3) $\delta = 0.2$

(4) $\delta = 0.1$

Fig 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

 $T_i = 150 \, ^{\circ}C$

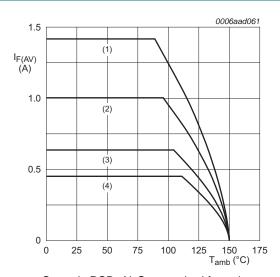
(1) $\delta = 1$

(2) $\delta = 0.5$

(3) $\delta = 0.2$

(4) $\delta = 0.1$

Fig 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

T_i = 150 °C

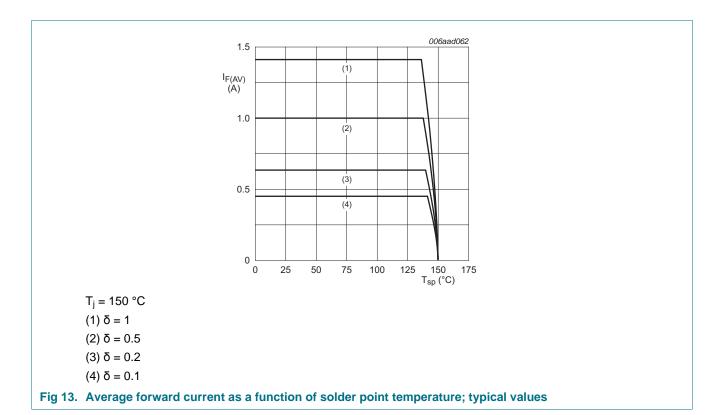
(1) $\delta = 1$

(2) $\delta = 0.5$

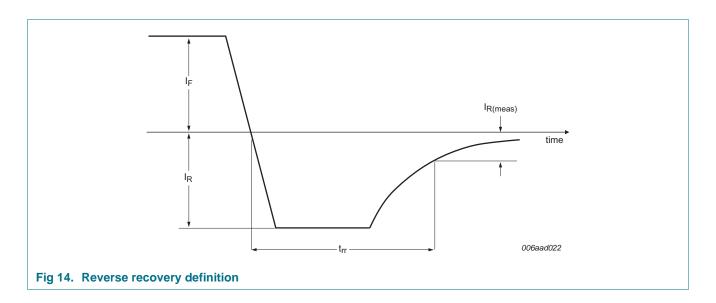
(3) $\delta = 0.2$

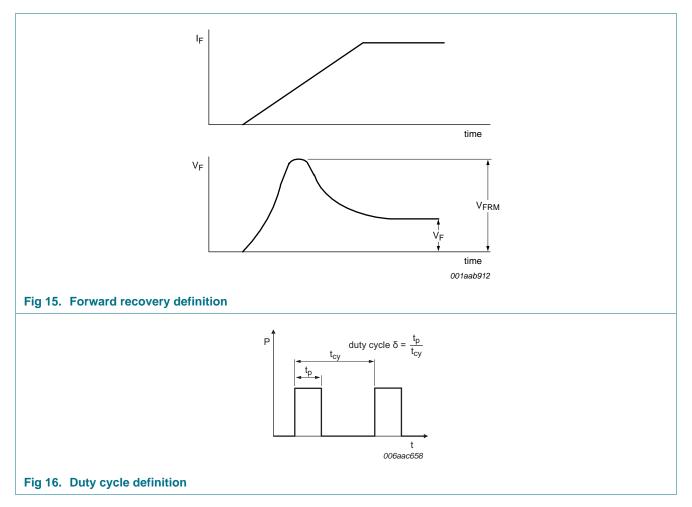
(4) $\delta = 0.1$

Fig 12. Average forward current as a function of ambient temperature; typical values



8. Test information



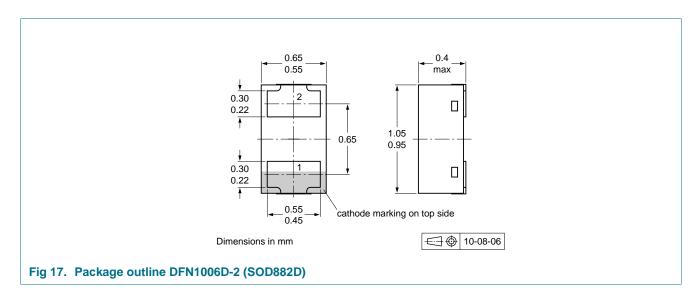


The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

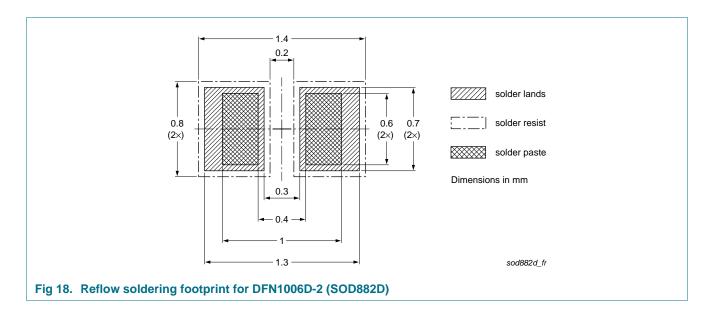
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------|--------------|--------------------|---------------|------------|
| PMEG2010BELD v.1 | 20120418 | Product data sheet | - | - |

12. Legal information

12.1 Data sheet status

| Document status[1] [2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URLhttp://www.nxp.com.

12.2 Definitions

Preview — The document is a preview version only. The document is still subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the

PMEG2010BELD

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2012. All rights reserved.

PMEG2010BELD

20 V, 1 A low VF MEGA Schottky barrier rectifier

Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published athttp://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Adelante, Bitport, Bitsound, CoolFlux, CoReUse, DESFire, EZ-HV, FabKey, GreenChip, HiPerSmart, HITAG, I²C-bus logo, ICODE, I-CODE, ITEC, Labelution, MIFARE, MIFARE Plus, MIFARE Ultralight, MoReUse, QLPAK, Silicon

Tuner, SiliconMAX, SmartXA, STARplug, TOPFET, TrenchMOS, TriMedia and UCODE — are trademarks of NXP B.V.

 $\ensuremath{\mathsf{HD}}$ $\ensuremath{\mathsf{Radio}}$ of logo — are trademarks of iBiquity Digital Corporation.

13. Contact information

For more information, please visit:http://www.nxp.com

For sales office addresses, please send an email to:salesaddresses@nxp.com

PMEG2010BELD

20 V, 1 A low VF MEGA Schottky barrier rectifier

14. Contents

| 1 | Product profile | 1 |
|------|-------------------------|---|
| 1.1 | General description | 1 |
| 1.2 | Features and benefits | 1 |
| 1.3 | Applications | 1 |
| 1.4 | Quick reference data | 1 |
| 2 | Pinning information | 2 |
| 3 | Ordering information | 2 |
| 4 | Marking | 2 |
| 5 | Limiting values | 3 |
| 6 | Thermal characteristics | 3 |
| 7 | Characteristics | 5 |
| 8 | Test information | 8 |
| 8.1 | Quality information | 9 |
| 9 | Package outline | 0 |
| 10 | Soldering1 | 0 |
| 11 | Revision history1 | 1 |
| 12 | Legal information1 | 2 |
| 12.1 | Data sheet status | 2 |
| 12.2 | Definitions1 | |
| 12.3 | Disclaimers | 2 |
| 12.4 | Trademarks1 | |
| 13 | Contact information 1 | 3 |

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.